

- AVAILABLE IN JAN, JANTX AND JANTXV
PER MIL-PRF-19500/118
- GENERAL PURPOSE SILICON DIODES
- METALLURGICALLY BONDED

1N5194UR
1N5195UR
1N5196UR
CDLL5194
CDLL5195
CDLL5196

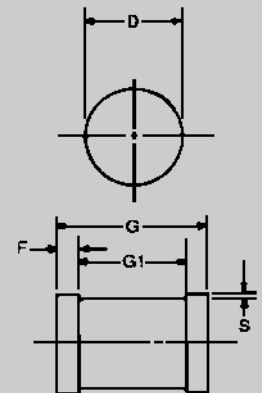
MAXIMUM RATINGS

Operating Temperature: -65°C to +175°C
Storage Temperature: -65°C to +175°C
Operating Current: 200 mA
Derating: 1.2mA/°C from 25°C to 150°C
1.0mA/°C from 150°C to 175°C
Forward Current: 650mA

ELECTRICAL CHARACTERISTICS @ 25°C, unless otherwise specified

TYPE	V _{RM}	V _{RWM}	I _O	I _O T _A = +150°C	I _{FSM} T _P = 1/120 S T _A = 25°C
	V(pk)	V(pk)	mA	mA	A
CDLL, 1N5194UR	80	70	200	50	2
CDLL, 1N5195UR	180	180	200	50	2
CDLL, 1N5196UR	250	225	200	50	2

TYPE	V _F @100mA	I _{R1} at V _{RWM}	I _{R2} at V _{RM} T _A = 25°C	I _{R3} at V _{RWM} T _A = 150°C
	V dc	nA dc	μA	μA dc
CDLL, 1N5194UR	0.8 - 1.0	25	100	5
CDLL, 1N5195UR	0.8 - 1.0	25	100	5
CDLL, 1N5196UR	0.8 - 1.0	25	100	5



DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
D	1.60	1.70	0.063	0.067
F	0.41	0.55	0.016	0.022
G	3.30	3.70	.130	.146
G1	2.54 REF.		.100 REF.	
S	0.03 MIN.		.001 MIN.	

FIGURE 1

DESIGN DATA

CASE: DO-213AA, Hermetically sealed glass case. (MELF, SOD-80, LL34)

LEAD FINISH: Tin / Lead

THERMAL RESISTANCE: (R_{QJEC}):
100 °C/W maximum

THERMAL IMPEDANCE: (Z_{QJX}): 70
°C/W maximum

POLARITY: Cathode end is banded.

MOUNTING POSITION: Any.

MOUNTING SURFACE SELECTION:
The Axial Coefficient of Expansion (COE) Of this Device is Approximately +6PPM/°C. The COE of the Mounting Surface System Should Be Selected To Provide A Suitable Match With This Device.



IN5194UR thru IN5196UR, CDLL5194 thru CDLL5196

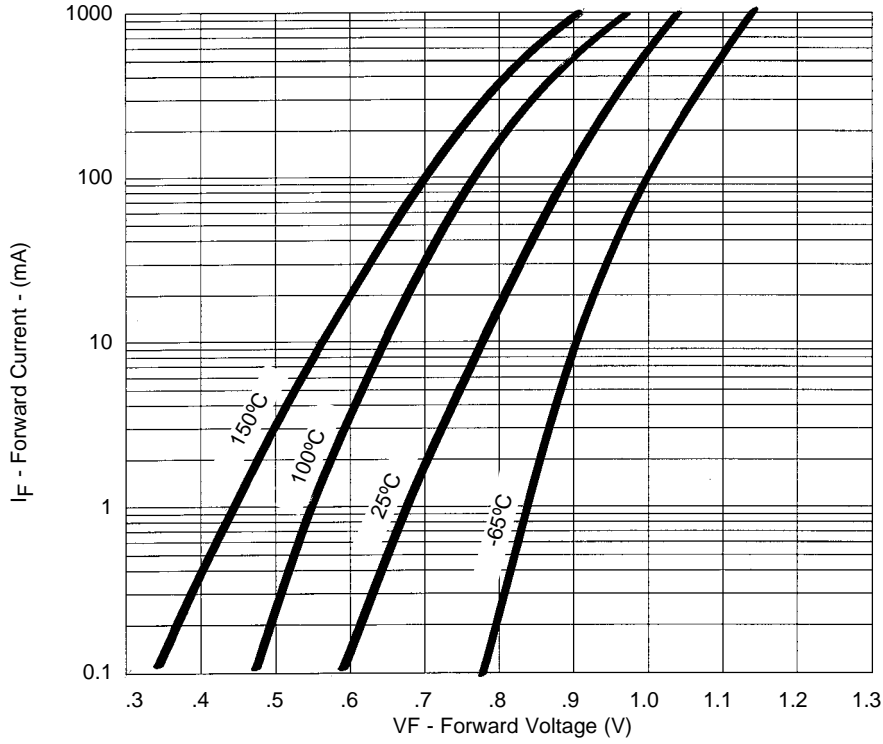
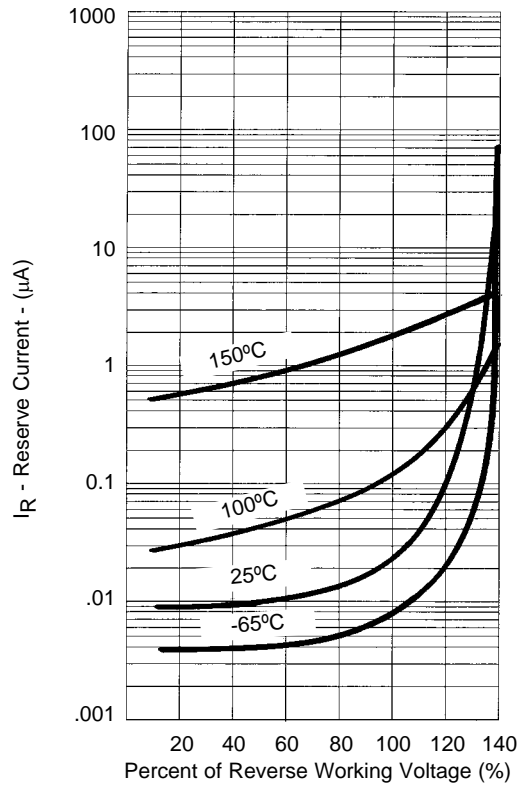


FIGURE 2
Typical Forward Current
vs Forward Voltage



NOTE : All temperatures shown on graphs are junction temperatures

FIGURE 3
Typical Reverse Current
vs Reverse Voltage